TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

TC7S08F, TC7S08FU

2-INPUT AND GATE

The TC7S08 is a high speed C²MOS 2-INPUT AND GATE fabricated with silicon gate C²MOS technology. It achieves high speed operation similar to equivalent LSTTL while maintaining the C²MOS low power dissipation.

The internal circuit is composed of 2 stages including buffer output, which enables high noise immunity and stable output.

All inputs are equipped with protection circuits against static discharge or transient excess voltage.

Output currents are 1/2 compared to TC74HC series models.

FEATURES

- Low Power Dissipation I_{CC} = 1µA (Max.) at Ta = 25°C
- High Noise Immunity
 VNIH = VNIL = 28% VCC (Min.)
- Output Drive Capability 5 LSTTL Loads
- Symmetrical Output Impedance ... |IOH| = IOL
- Balanced Propagation Delays t_{pLH}≒t_{pHL}
- Wide Operating Voltage Range ... V_{CC} (opr) = 2~6V

MAXIMUM RATINGS

CHARACTERISTIC	SYMBOL	RATING	UNIT
Supply Voltage Range	Vcc	-0.5~7	V
DC Input Voltage	v_{IN}	-0.5~V _{CC} +0.5	V
DC Output Voltage	Vout	-0.5~V _{CC} +0.5	V
Input Diode Current	lικ	± 20	mA
Output Diode Current	lок	± 20	mA
DC Output Current	Ιουτ	± 12.5	mΑ
DC V _{CC} /Ground Current	lcc	± 25	mA
Power Dissipation	PD	200	mW
Storage Temperature	T _{stg}	- 65~150	°C
Lead Temperature (10s)	тլ	260	°C



Weight SSOP5-P-0.95 : 0.016g (Typ.) SSOP5-P-0.65A : 0.006g (Typ.)

MARKING



PIN ASSIGNMENT (TOP VIEW)



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= 2mA (Min.)

LOGIC DIAGRAM

(1) (4) OUT Y IN B-(2) & IN A

RECOMMENDED OPERATING CONDITIONS

CHARACTERISTIC	SYMBOL	RATING	UNIT
Supply Voltage	Vcc	2~6	V
Input Voltage	V _{IN} 0~V _{CC}		V
Output Voltage	Vout	0~V _{CC}	V
Operating Temperature	T _{opr}	- 40~85	°C
		0~1000 (V _{CC} = 2.0V)	
Input Rise and Fall Time	t _r , t _f	$0 \sim 500 (V_{CC} = 4.5V)$	ns
		$0 \sim 400 \ (V_{CC} = 6.0V)$	

DC ELECTRICAL CHARACTERISTICS

CHARACTERISTIC SYMBO		TEST CONDITION			Ta = 25°C			Ta = −40~85°C		UNIT
CHARACTERISTIC			Vcc	MIN.	TYP.	MAX.	MIN.	MAX.		
				2.0	1.5	—	—	1.5	—	
High-Level	VIH		—	4.5	3.15	—	_	3.15	_	V
Input Voltage				6.0	4.2	—	—	4.2		
				2.0	—	_	0.5	_	0.5	
Low-Level	VIL		—	4.5	—	—	1.35	—	1.35	V
Input Voltage				6.0	—	_	1.8	—	1.8	
High-Level Output Voltage		V _{IN} = V _{IH}		2.0	1.9	2.0	_	1.9	_	
	Voн		I _{OH} = -20μA	4.5	4.4	4.5		4.4	_	
				6.0	5.9	6.0		5.9	_	v
			$I_{OH} = -2mA$	4.5	4.18	4.31	—	4.13	—	
			I _{OH} = - 2.6mA	6.0	5.68	5.80	—	5.63		
		V _{IN} = V _{IH} or V _{IL}		2.0	—	0.0	0.1	_	0.1	
Low-Level Output Voltage			l _{OL} =20μΑ	4.5	—	0.0	0.1	—	0.1	
	VOL			6.0	—	0.0	0.1	_	0.1	v
			I _{OL} = 2mA	4.5	—	0.17	0.26	—	0.33	
			I _{OL} = 2.6mA	6.0	—	0.18	0.26	—	0.33	
Input Leakage Current	IIN	V _{IN} = V _{CC} or GND		6.0	_	_	±0.1	—	± 1.0	
Quiescent Supply Current	lcc	$V_{IN} = V_{CC}$ or GND		6.0	_		1.0	_	10.0	μA

Output currents are 1/2 compared to TC74HC series models.

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CHARACTERISTIC	SYMBOL	TEST CONDITION	Ta = 25°C			UNIT
CHARACTERISTIC	STIVIBUL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Output Transition	ttlh			5	10	ns
Time	tthl			,	10	115
Propagation Delay	t _{pLH}			7	15	ns
Time	t _{pHL}	_		/		115

AC ELECTRICAL CHARACTERISTICS ($C_L = 15pF$, Input $t_r = t_f = 6ns$, $V_{CC} = 5V$)

AC ELECTRICAL CHARACTERISTICS ($C_L = 50pF$, Input $t_r = t_f = 6ns$)

CHARACTERISTIC SYMBO	SYMBOL			Ta = 25°C			Ta = -4	UNIT	
CHARACTERISTIC	CHARACTERISTIC STMBOL			MIN.	TYP.	MAX.	MIN.	MAX.	
Output Transition	t			—	50	125	—	155	
Output Transition t _{TLH} Time t _{THL}		4.5		14	25	_	31	ns	
	U HL		6.0	_	12	21	—	26	
Propagation Delay t _{pLH} Time t _{pHL}	1		2.0	_	48	100	_	125	
	-	4.5		12	20		25	ns	
		6.0	_	9	17		21		
Input Capacitance	CIN	_		—	5	10		10	
Power Dissipation Capacitance	C _{PD}	(Note 1)		_	10	_	_	_	рF

Note 1 : C_{PD} defined as the value of internal equivalent capacitance of IC which is calculated from the operating current consumption without load (refer to Test Circuit).

Average operating current can be obtained by the equation here under. I_{CC} (opr) = CPD·V_{CC}·f_{IN} + I_{CC}

SWITCHING CHARACTERISTICS TEST CIRCUIT





ICC (opr) TEST CIRCUIT



Input waveform is the same as that in case of switching characteristics test.

OUTLINE DRAWING SSOP5-P-0.95

Unit : mm





Weight : 0.016g (Typ.)

OUTLINE DRAWING SSOP5-P-0.65A

Unit : mm





Weight : 0.006g (Typ.)